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(54) Title: NANOWIRE LED STRUCTURE AND METHOD FOR MANUFACTURING THE SAME

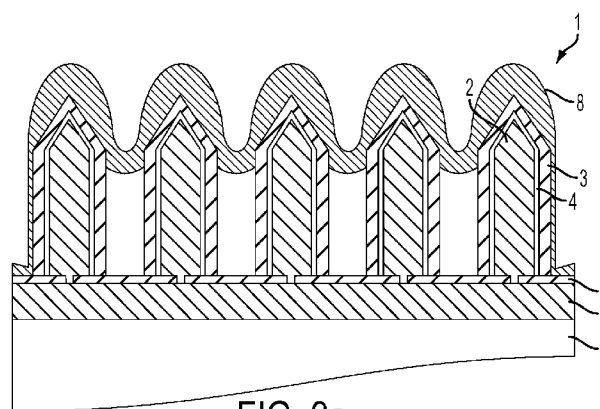


FIG. 3a

(57) Abstract: A light emitting diode (LED) structure includes a plurality of devices arranged side by side on a support layer. Each device includes a first conductivity type semiconductor nanowire core and an enclosing second conductivity type semiconductor shell for forming a pn or pin junction that in operation provides an active region for light generation. A first electrode layer extends over the plurality of devices and is in electrical contact with at least a top portion of the devices to connect to the shell. The first electrode layer is at least partly air-bridged between the devices.